

L Number	Hits	Search Text	DB	Time stamp
2	10	5786275.pn. 6482743.pn. 6451697.pn. 6569349.pn. 6579153.pn. 6602436.pn. 6616717.pn. 20010024933.pn. 20020058426.pn. 20030022497.pn.	USPAT; US-PGPUB	2004/01/05 10:08
3	39	5676587.pn. 5853604.uref. 5827781.uref.	USPAT; US-PGPUB	2004/01/05 11:49
4	8	5733177.uref.	USPAT; US-PGPUB	2004/01/05 12:01
5	16	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal))) same (relative near2 (speed velocity))	USPAT; US-PGPUB	2004/01/05 12:02
6	132	((438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative near2 (speed velocity))) and ((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal))	USPAT; US-PGPUB	2004/01/05 12:15
7	8	((438/626.ccls. 438/633.ccls. 438/687.ccls.) and (438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.)) and (relative near2 (speed velocity))	USPAT; US-PGPUB	2004/01/05 12:44
8	25	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal))) same ((relative linear) near2 (speed velocity))	USPAT; US-PGPUB	2004/01/05 12:49
9	28	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal))) same ((rotat\$6 near2 (speed velocity)) rpm rpms) same (change decreas\$4 reduc\$5)	USPAT; US-PGPUB	2004/01/05 12:56
10	4	((cmp (chemical near mechanical)) with (copper cu conduct\$4 metal))) and (relative near2 (speed velocity))	EPO; JPO; DERWENT; IBM_TDB	2004/01/05 13:08
11	109	(cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring) same membrane same (platen pad) same (pressure psi pa)) and (wafer substrate)	USPAT; US-PGPUB	2004/01/05 13:09
12	146	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and ((cmp (chemical near mechanical) polish\$4) with (copper cu conduct\$4 metal)) and ((carrier head) same (retain\$4 ring membrane) same (platen pad) same (pressure psi pa)) and (wafer substrate))	USPAT; US-PGPUB	2004/01/05 13:52
13	137	((cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane)) and (platen pad)) and (pressure psi pa copper cu metal conduct\$4)	EPO; JPO; DERWENT; IBM_TDB	2004/01/05 14:15
14	6	(cmp (chemical near mechanical) polish\$4) and (wafer substrate) and ((carrier head) same (platen pad) same (rpm adj second))	USPAT; US-PGPUB	2004/01/05 14:22
15	0	(cmp (chemical near mechanical) polish\$4) and (wafer substrate) and ((carrier head) same (platen pad) same ((rpm rotat\$6) near accelerat\$5))	USPAT; US-PGPUB	2004/01/05 14:31
16	2	(cmp (chemical near mechanical) polish\$4) and (wafer substrate) and ((carrier head) same (platen pad) same ((rpm rotat\$6) with accelerat\$5))	USPAT; US-PGPUB	2004/01/05 14:31
17	30	(cmp (chemical near mechanical) polish\$4) and (wafer substrate) and ((carrier head) same (platen pad) same accelerat\$5)	USPAT; US-PGPUB	2004/01/05 14:33
19	480	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative near2 (speed velocity))	USPAT; US-PGPUB	2004/01/05 14:36
20	626	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and ((cmp (chemical near mechanical) polish\$4) and ((carrier head) same (retain\$4 ring membrane)) and (wafer substrate) and (platen pad))	USPAT; US-PGPUB	2004/01/05 14:43